Adriano Cola

List of Publications by Year
in descending order

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147 papers	1,737 citations	331538 21 h-index	395590 33 g-index
149 all docs	149 docs citations	149 times ranked	1579 citing authors

#	Article	IF	Citations
1	The polarization mechanism in CdTe Schottky detectors. Applied Physics Letters, 2009, 94, .	1.5	108
2	Increase of charge carriers density and reduction of Hall mobilities in oxygen-plasma treated indiumâ€“tinâ€“oxide anodes. Applied Physics Letters, 1999, 75, 19-21.	1.5	94
3	Photoconduction Properties in Aligned Assemblies of Colloidal CdSe/CdS Nanorods. ACS Nano, 2010, 4, 1646-1652.	7.3	73
4	Study on Instability Phenomena in CdTe Diode-Like Detectors. IEEE Transactions on Nuclear Science, 2009, 56, 1736-1742.	1.2	53
5	Electric Field Properties of CdTe Nuclear Detectors. IEEE Transactions on Nuclear Science, 2007, 54, 868-872.	1.2	44
6	Capacitive RF MEMS Switches With Tantalum-Based Materials. Journal of Microelectromechanical Systems, 2011, 20, 365-370.	1.7	39
7	Spectroscopic response of a CdZnTe multiple electrode detector. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2007, 583, 324-331.	0.7	35
8	Optical and electrical properties of polycarbonate layers implanted by high energy Cu ions. Nuclear Instruments & Methods in Physics Research B, 2013, 312, 42-47.	0.6	35
9	Investigation of the electric field distribution in x-ray detectors by Pockels effect. Journal of Optics, 2006, 8, S467-S472.	1.5	33
10	On hydrogen transport VPE-grown CdTe epilayers for fabrication of 1â€“100keV X-ray detectors. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2001, 458, 1-6.	0.7	32
11	Current transport in Schottky barriers prepared by ion beam sputtering. Solid-State Electronics, 1995, 38, 1923-1928.	0.8	31
12	Band discontinuities at beta -FeSi2/Si heterojunctions as deduced from their photoelectric and electrical properties. Semiconductor Science and Technology, 1994, 9, 1395-1403.	1.0	30
13	On the electrostatic actuation of capacitive RF MEMS switches on GaAs substrate. Sensors and Actuators A: Physical, 2015, 232, 202-207.	2.0	29
14	Phototransport in networks of tetrapod-shaped colloidal semiconductor nanocrystals. Nanoscale, 2010, 2, 2171.	2.8	28
15	Evaluation of semi-insulating InP crystals for nuclear radiation. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1996, 373, 47-50.	0.7	26
16	Field-assisted capture of electrons in semi-insulating GaAs. Journal of Applied Physics, 1997, 81, 997-999.	1.1	26
17	Charge Transients by Variable Wavelength Optical Pulses in CdTe Nuclear Detectors. IEEE Transactions on Nuclear Science, 2012, 59, 1569-1574.	1.2	26
18	An extended drift-diffusion model of semi-insulating n-GaAs Schottky-barrier diodes. Semiconductor Science and Technology, 1997, 12, 1358-1364.	1.0	25

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19	Polarization anisotropy of individual core/shell GaAs/AlGaAs nanowires by photocurrent spectroscopy. Applied Physics Letters, 2011, 98, .	1.5	25
20	Electric fields and dominant carrier transport mechanisms in CdTe Schottky detectors. Applied Physics Letters, 2013, 102, .	1.5	25
21	Role of charge separation on two-step two photon absorption in InAs/GaAs quantum dot intermediate band solar cells. Applied Physics Letters, 2016, 108, .	1.5	25
22	On direct-writing methods for electrically contacting GaAs and Ge nanowire devices. Applied Physics Letters, 2010, 96, 223107.	1.5	23
23	An Unconventional Hybrid Variable Capacitor With a 2-D Electron Gas. IEEE Transactions on Electron Devices, 2014, 61, 445-451.	1.6	22
24	Characterization of a defect layer at a Schottky barrier interface by current and capacitance measurements. Solid-State Electronics, 1993, 36, 785-789.	0.8	21
25	Reliability Enhancement by Suitable Actuation Waveforms for Capacitive RF MEMS Switches in IIIâ€“V Technology. Journal of Microelectromechanical Systems, 2012, 21, 414-419.	1.7	21
26	Electric Field and Current Transport Mechanisms in Schottky CdTe X-ray Detectors under Perturbing Optical Radiation. Sensors, 2013, 13, 9414-9434.	2.1	21
27	Resonant-cavity-enhanced heterostructure metalâ€“semiconductorâ€“metal photodetector. Applied Physics Letters, 2002, 80, 3222-3224.	1.5	20
28	Optically Modulated High-Sensitivity Heterostructure Varactor. IEEE Electron Device Letters, 2006, 27, 710-712.	2.2	19
29	Towards an electronic grade nanoparticle-assembled silicon thin film by ballistic deposition at room temperature: the deposition method, and structural and electronic properties. Journal of Materials Chemistry C, 2017, 5, 3725-3735.	2.7	19
30	Ti/GaAs Schottky barriers prepared by ion beam sputtering. Journal of Applied Physics, 1992, 71, 4966-4971.	1.1	18
31	Charge carrier transport in thin films of colloidal CdSe quantum rods. Journal of Applied Physics, 2008, 104, 074306.	1.1	18
32	Transport and charging mechanisms in Ta2O5 thin films for capacitive RF MEMS switches application. Journal of Applied Physics, 2010, 107, .	1.1	18
33	Comparative study of metal and non-metal ion implantation in polymers: Optical and electrical properties. Nuclear Instruments & Methods in Physics Research B, 2014, 331, 168-171.	0.6	18
34	Photodetectors based on heterostructures for opto-electronic applications. IEEE Transactions on Microwave Theory and Techniques, 2003, 51, 2063-2072.	2.9	17
35	CdTe X-ray detectors under strong optical irradiation. Applied Physics Letters, 2014, 105, .	1.5	17
36	Some new results on semi-insulating GaAs detectors for low energy X-rays. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1995, 355, 425-427.	0.7	16

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37	Spectroscopic performance of semi-insulating GaAs detectors for digital radiography. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1999, 422, 247-251.	0.7	16
38	A highly tunable heterostructure metal-semiconductor-metal capacitor utilizing embedded 2-dimensional charge. Applied Physics Letters, 2012, 100, 153505.	1.5	16
39	In-plane Aligned Colloidal 2D WS2 Nanoflakes for Solution-Processable Thin Films with High Planar Conductivity. Scientific Reports, 2019, 9, 9002.	1.6	16
40	Deep Level Transient Spectroscopy of Mo/GaAs Schottky Barriers Prepared by DC Sputtering. Physica Status Solidi A, 1991, 124, 473-481.	1.7	15
41	Reverse current in SI GaAs pixel detectors. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1998, 410, 85-91.	0.7	15
42	Electron cloud effect on current injection across a Schottky contact. Applied Physics Letters, 2000, 77, 4007-4009.	1.5	15
43	Hall measurements of treated indium tin oxide surfaces. Synthetic Metals, 2000, 111-112, 363-367.	2.1	15
44	Electric field distribution and charge transport properties in diode-like CdTe X-ray detectors. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2006, 568, 406-411.	0.7	15
45	Time Response of Two-Dimensional Gas-Based Vertical Field Metalâ€“Semiconductorâ€“Metal Photodetectors. IEEE Transactions on Electron Devices, 2008, 55, 1762-1770.	1.6	15
46	Ta₂O₅Thin Films for Capacitive RF MEMS Switches. Journal of Sensors, 2010, 2010, 1-5.	0.6	15
47	Low-temperature grown GaAs heterojunction metal-semiconductor-metal photodetectors improve speed and efficiency. Applied Physics Letters, 2011, 99, .	1.5	14
48	Experimental study of LEC GaAs detectors for X-ray digital radiography. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1996, 380, 410-413.	0.7	13
49	Electrical and optical properties of ITO and ITO/Cr-doped ITO films. Applied Physics A: Materials Science and Processing, 2010, 101, 753-758.	1.1	13
50	Subgap time of flight: A spectroscopic study of deep levels in semi-insulating CdTe:Cl. Journal of Applied Physics, 2016, 119, .	1.1	13
51	Preparation and characterisation of organicâ€“inorganic heterojunction based on BDA-PPV/CdS nanocrystals. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2000, 74, 175-179.	1.7	12
52	Charge transients locally induced by laser pulses in CdTe planar and multi-strip detectors. IEEE Transactions on Nuclear Science, 2005, 52, 1968-1974.	1.2	12
53	An original method to evaluate the transport parameters and reconstruct the electric field in solid-state photodetectors. Applied Physics Letters, 2014, 104, 193503.	1.5	12
54	Structural and electrical properties of CdTe layers grown on ZnTe/GaAs by hydrogen transport VPE. Journal of Crystal Growth, 2000, 214-215, 229-233.	0.7	11

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55	High-Speed, High-Sensitivity Optoelectronic Device with Bilayer Electron and Hole Charge Plasma. ACS Photonics, 2014, 1, 560-569.	3.2	11
56	Electrical characterization and detector performances of a LPE GaAs detector for X-ray digital radiography. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1994, 346, 372-378.	0.7	10
57	Direct assessment of tunable Schottky barriers by internal photoemission spectroscopy. Applied Physics Letters, 1998, 73, 259-261.	1.5	10
58	Transparent ZnO ohmic contact on semi-insulating GaAs. Solid-State Electronics, 1999, 43, 2021-2024.	0.8	10
59	Hard x-ray polarimetry with a thick CdTe position sensitive spectrometer. , 2000, , .		10
60	Spectroscopic response of a CdTe microstrip detector when irradiated at various impinging angles. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2004, 531, 125-133.	0.7	10
61	Spectroscopic Response of CZT Detectors Obtained by the Boron Oxide Encapsulated Vertical Bridgman Method. IEEE Transactions on Nuclear Science, 2011, 58, 552-558.	1.2	10
62	Anomalous Capacitance Enhancement Triggered by Light. IEEE Journal of Selected Topics in Quantum Electronics, 2015, 21, 1-5.	1.9	10
63	A study of the trap influence on the performance of semi-insulating GaAs detectors. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1997, 395, 349-354.	0.7	9
64	Development of semi-insulating GaAs detectors for digital radiography. Nuclear Physics, Section B, Proceedings Supplements, 1998, 61, 633-637.	0.5	9
65	An AlGaAs-GaAs-based RCE MSM photodetector with delta modulation doping. IEEE Electron Device Letters, 2003, 24, 312-314.	2.2	9
66	Photocurrent properties of single GaAs/AlGaAs coreâ€“shell nanowires with Schottky contacts. Nanotechnology, 2012, 23, 465701.	1.3	9
67	A method for the determination of barrier heights from the capacitance-voltage characteristics of a Schottky junction containing bulk deep traps. Solid-State Electronics, 1995, 38, 989-995.	0.8	8
68	Electrical characterization and detection performances of various semi-insulating GaAs crystals for low energy gamma-rays. IEEE Transactions on Nuclear Science, 1995, 42, 254-257.	1.2	8
69	Triple Ion Beam Sputtering Deposition of Î²-FeSi₂. Materials Science Forum, 1996, 203, 173-180.	0.3	8
70	HETERODIMENSIONAL CONTACTS AND OPTICAL DETECTORS. International Journal of High Speed Electronics and Systems, 2000, 10, 375-386.	0.3	8
71	Investigation on semi-insulating GaAs detectors using laser-induced current pulses. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2001, 458, 158-163.	0.7	8
72	New configuration of metallic photocathodes prepared by pulsed laser deposition. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2013, 724, 72-75.	0.7	8

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73	Performance Enhancement of a GaAs Detector with a Vertical Field and an Embedded Thin Low-Temperature Grown Layer. Sensors, 2013, 13, 2475-2483.	2.1	8
74	Inter-level carrier dynamics and photocurrent generation in large band gap quantum dot solar cell by multistep growth. Solar Energy Materials and Solar Cells, 2017, 171, 142-147.	3.0	8
75	X-ray imaging using a pixel GaAs detector. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1995, 362, 547-550.	0.7	7
76	Electronic structure of double stacked InAsâˆ•GaAs quantum dots: Experiment and theory. Journal of Applied Physics, 2007, 102, 094314.	1.1	7
77	Hydrogen transport vapor phase epitaxy of CdTe on hybrid substrates for x-ray detector applications. Journal of Electronic Materials, 1999, 28, 695-699.	1.0	6
78	Detection performance of SI GaAs detectors for nuclear medicine. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2001, 460, 123-126.	0.7	6
79	Simulated and experimental spectroscopic performance of GaAs X-ray pixel detectors. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2001, 466, 188-193.	0.7	6
80	Simulation of the collection properties of CdTe strip detectors. IEEE Transactions on Nuclear Science, 2001, 48, 292-295.	1.2	6
81	High speed photodetectors based on a two-dimensional electron/hole gas heterostructure. Applied Physics Letters, 2013, 102, 161108.	1.5	6
82	Electrical properties of planar AlGaN/GaN Schottky diodes: Role of 2DEG and analysis of non-idealities. Journal of Applied Physics, 2017, 121, 135701.	1.1	6
83	A study of the electrical and charge-collection properties of semi-insulating GaAs detectors. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1996, 380, 66-69.	0.7	5
84	Charge trapping and currentâ€“voltage bistability in InGaAs quantum wires. Journal of Applied Physics, 1996, 80, 936-940.	1.1	5
85	Heterojunction and heterodimensional devices for optoelectronics. IEEE Microwave Magazine, 2001, 2, 40-45.	0.7	5
86	A study of the spectroscopic performance of a CdTe microstrip detector. IEEE Transactions on Nuclear Science, 2003, 50, 1026-1030.	1.2	5
87	Fabrication of Photonic Crystal Structures by Electron Beam Lithography. , 2006, , .		5
88	Optimization of electron beam induced deposition process for the fabrication of diode-like Pt/SiO2/W devices. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2013, 31, 041805.	0.6	5
89	On the spatial inhomogeneity of charge generation and collection in inverted all polymer solar cells. Applied Physics Letters, 2013, 103, 053305.	1.5	5
90	On the homogeneity of the external quantum efficiency in a free OPV roll-to-roll flexible solar module. Synthetic Metals, 2019, 247, 248-254.	2.1	5

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91	Determination of deepâ€level parameters by a new analysis method of isothermal capacitance transients. Journal of Applied Physics, 1991, 69, 3072-3076.	1.1	4
92	Microscopic modelling of semi-insulating GaAs detectors. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1997, 395, 98-100.	0.7	4
93	A percolative simulation of dielectric-like breakdown. Microelectronics Reliability, 1998, 38, 249-253.	0.9	4
94	Monte Carlo simulation of the induced signal in semi-insulating GaAs detectors. Applied Physics Letters, 1998, 73, 1709-1711.	1.5	4
95	La_{0.7}Sr_{0.3}MnO₃ thin films deposited by pulsed laser ablation for spintronic applications. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 1817-1820.	0.8	4
96	Giant light-induced capacitance enhancements in an unconventional capacitor with two-dimensional hole gas. , 2012, , .		4
97	On the relation between deep level compensation, resistivity and electric field in semi-insulating CdTe:Cl radiation detectors. Semiconductor Science and Technology, 2016, 31, 12LT01.	1.0	4
98	Optically activated planar GaAs switches for DC applications. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1998, 418, 434-439.	0.7	3
99	GaAs devices with vertical and planar structures for optically activated high-voltage switching. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1998, 417, 124-130.	0.7	3
100	Investigation of charge collection properties of CdTe detectors by optical pulses. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2004, 518, 571-573.	0.7	3
101	Optical and Electrical Characterization of GaAs-Based High-Speed and High-Sensitivity Delta-Doped Resonant Cavity-Enhanced HMSM Photodetector. IEEE Transactions on Electron Devices, 2005, 52, 454-464.	1.6	3
102	Electric Field Properties of CdTe Nuclear Detectors. , 2006, , .		3
103	On the transmission of terahertz radiation through silicon-based structures. Journal of Applied Physics, 2014, 116, 044504.	1.1	3
104	Photocurrent spectroscopy of ZnCdSe/ZnSe multiple quantum wells. Superlattices and Microstructures, 1994, 16, 363-365.	1.4	2
105	SI-GaAs detectors with epitaxial junction. IEEE Transactions on Nuclear Science, 1999, 46, 171-175.	1.2	2
106	Study of GaAs detectors characteristics for medical imaging. , 0, , .		2
107	An overview on performance and possible applications of X- and gamma-ray semiconductor detectors irradiated at various impinging angles. IEEE Transactions on Nuclear Science, 2004, 51, 1216-1223.	1.2	2
108	Study of the spectral response of CZT multiple-electrode detectors. , 2007, , .		2

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109	Development of a homoepitaxial technology for fabrication of X- and Î³-ray detectors based on CdTe p-i-n diodes. Nuclear Physics, Section B, Proceedings Supplements, 2007, 166, 262-265.	0.5	2
110	Role of defect states on electrical and optical properties in CdSe nanorod thin films. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 2063-2065.	1.3	2
111	Development of capacitive RF MEMS switches with TaN and Ta 2 O 5 thin films. Proceedings of SPIE, 2011, , .	0.8	2
112	Non-conventional photocathodes based on Cu thin films deposited on Y substrate by sputtering. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2014, 752, 27-32.	0.7	2
113	Study of spatial inhomogeneity in inverted all-polymer solar cells: Effect of solvent and annealing. Journal of Polymer Science, Part B: Polymer Physics, 2015, 53, 804-813.	2.4	2
114	High Speed Heterostructure Metal-Semiconductor-Metal Photodetectors. Acta Physica Polonica A, 2005, 107, 14-25.	0.2	2
115	Overcoming Transit Time Limitations with Collective Excitations. , 2013, , .		2
116	Optical Writing and Electro-Optic Imaging of Reversible Space Charges in Semi-Insulating CdTe Diodes. Sensors, 2022, 22, 1579.	2.1	2
117	Deep-level spectroscopy by analysis of isothermal capacitance transients. Nuovo Cimento Della Societa Italiana Di Fisica D - Condensed Matter, Atomic, Molecular and Chemical Physics, Biophysics, 1990, 12, 1443-1451.	0.4	1
118	Modeling of the Signal Induced by an Incident Radiation in Semi-Insulating GaAs Detectors. Materials Research Society Symposia Proceedings, 1997, 487, 453.	0.1	1
119	Monte Carlo simulator of the charge signal induced by external radiation on semi-insulating GaAs detectors. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1999, 434, 67-70.	0.7	1
120	Irradiation of optically activated SI-GaAs high-voltage switches with low and high energy protons. IEEE Transactions on Nuclear Science, 1999, 46, 121-125.	1.2	1
121	Evidence for charge gain mechanism in SI-GaAs detectors with epitaxial junction. IEEE Transactions on Nuclear Science, 2000, 47, 780-783.	1.2	1
122	Carrier dynamics in InAs quantum dots investigated by current transient response to quasi-resonant interband excitation. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 2119-2121.	1.3	1
123	Study on instability phenomena in CdTe diode-like detectors. , 2008, , .		1
124	Single-Layer InAs Quantum Dots for High-Performance Planar Photodetectors Near 1.3 $muhbox{m}$. IEEE Transactions on Electron Devices, 2010, 57, 1237-1242.	1.6	1
125	Charge transients by variable wavelength optical pulses in CdTe nuclear detectors. , 2011, , .		1
126	A Planar Switchable Capacitor with Embedded Two-Dimensional Electron System for Higher Integrations in VLSI and RFIC. , 2012, , .		1

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127	Photoelectrical Properties of 1.3Î¼m Emitting InAs Quantum Dots in InGaAs Matrix. Acta Physica Polonica A, 2005, 107, 381-387.	0.2	1
128	Current bistability in InGaAs quantum wire p-i-n heterostructures. Solid-State Electronics, 1996, 40, 437-439.	0.8	0
129	Radiation damage tests of GaAs HV switches for MSGCs bias control. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1999, 426, 216-220.	0.7	0
130	Monte Carlo simulator for x-ray spectra analysis of GaAs detectors. , 1999, , .		0
131	<title>Vapor phase epitaxy growth of CdTe epilayers for RT x-ray detectors</title>. , 2000, , .		0
132	A novel HMSM photodetector with resonant cavity for short haul communications. , 0, , .		0
133	Photodetector with Internal Aiding Field Based-on GaAs/AlGaAs Heterostructures. , 2002, , .		0
134	Photodetectors based on heterostructures for optoelectronic applications. , 2002, 4919, 306.		0
135	<title>Nondestructive diagnostics of bulk GaAs and CdZnTe crystals by nanosecond and picosecond wave-mixing techniques</title>. , 2003, , .		0
136	The role of the AlGaAs doping level on the optical gain of two-dimensional electron gas photodetectors. Journal of Electronic Materials, 2004, 33, 123-127.	1.0	0
137	An overview on performance and possible applications of X- and gamma-ray semiconductor detectors irradiated at various impinging angles. , 0, , .		0
138	Modeling of a high sensitivity heterostructure varactor with optical modulation capability. , 2007, , .		0
139	A MOVPE Technology for Fabrication of CdTe-based Homoepitaxial p-i-n Diode Structures as Nuclear Radiation Detectors. , 2007, , .		0
140	Development of a new photodetector based on two dimensional hole gas. , 2007, , .		0
141	Investigation on the performances of multiple microstrip CdTe detectors. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2007, 573, 389-397.	0.7	0
142	High-speed high-responsivity low temperature grown GaAs detector. , 2012, , .		0
143	A Light-activated Quantum Capacitance Device as a Highly Tunable Variable Capacitor. , 2013, , .		0
144	Tailoring design and fabrication of capacitive RF MEMS switches for K-band applications. Proceedings of SPIE, 2015, , .	0.8	0

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145	Photoconduction Properties of Single GaAs/AlGaAs Core-Shell Nanowires. , 2013, , .		0
146	Electro-Optically Sampled Time Response of Core-Shell Nanowires. , 2017, , .		0
147	Optoelectronic Quantum Capacitors for Configurable Neural Photonic Networks. , 2019, , .		0